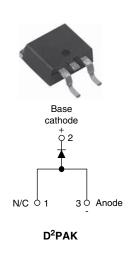


# HEXFRED® Ultrafast Soft Recovery Diode, 8 A



PRODUCT SUMMARY						
Package	TO-263AB (D <sup>2</sup> PAK)					
I <sub>F(AV)</sub>	8 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.7 V					
t <sub>rr</sub> (typ.)	18 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- · Specified at operating conditions
- AEC-Q101 qualified
- Material categorization:
   For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





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#### **BENEFITS**

- · Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA08TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the VS-HFA08TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB60S is ideally suited for applications in power supplies (PFC boost diode) and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	$V_R$		600	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8			
Single pulse forward current	I <sub>FSM</sub>		60	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		24			
Maximum navar discination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	36	w		
Maximum power dissipation		T <sub>C</sub> = 100 °C	14			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C		





<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	600	-	-			
	I <sub>F</sub> = 8.0 A			See fig. 1 -	-	1.4	1.7	V
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 16 A	-		1.7	2.1		
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7		
Maximum reverse		$V_R = V_R \text{ rated}$ $T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$ See fig. 2 —		-	0.3	5.0	μA	
leakage current	I <sub>RM</sub>			-	100	500	μΑ	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		=	10	25	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from pa	ackage body	=	8.0	=	nH	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (TJ = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS			TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 2$	$200 \text{ A/}\mu\text{s}, V_{\text{R}} = 30 \text{ V}$	-	18	-		
Reverse recovery time See fig. 5, 6	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 8.0 A dI <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 200 V	-	37	55	ns	
occ lig. 5, 6	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	55	90		
Peak recovery current	I <sub>RRM1</sub>	$T_J = 25  ^{\circ}C$		-	3.5	5.0	A nC	
r ear recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	4.5	8.0		
Reverse recovery charge	Q <sub>rr1</sub>	$T_J = 25  ^{\circ}C$		-	65	138		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	124	360	110	
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	240	-	- A/μs	
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	210	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	3.5	K/W		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	- r./vv		
Woight			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Marking device		Case style D <sup>2</sup> PAK		HFA08	TB60S			

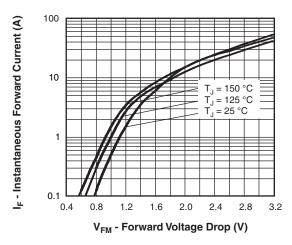


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

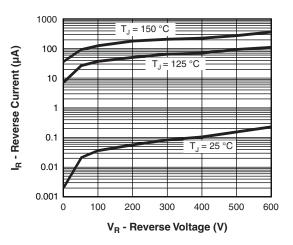


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

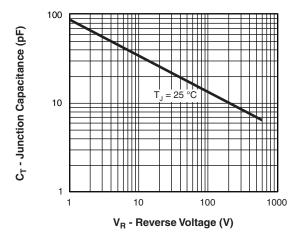


Fig. 1 - Typical Junction Capacitance vs. Reverse Voltage

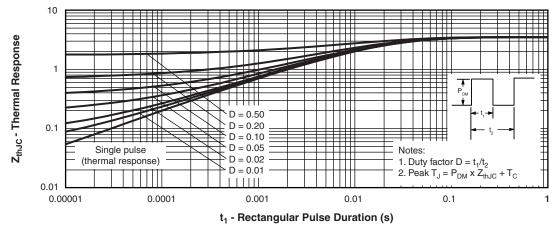


Fig. 2 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

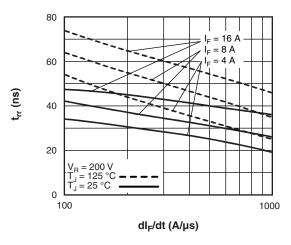


Fig. 3 - Typical Reverse Recovery Time vs.  $dI_F/dt$ 

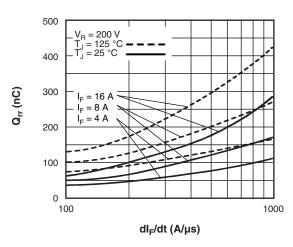


Fig. 5 - Typical Stored Charge vs. dl<sub>F</sub>/dt

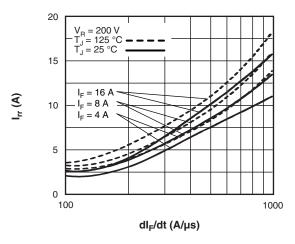


Fig. 4 - Typical Recovery Current vs. dl<sub>F</sub>/dt

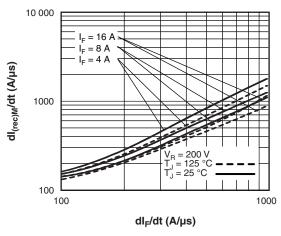


Fig. 6 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

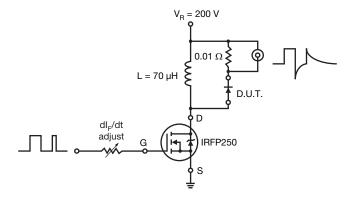
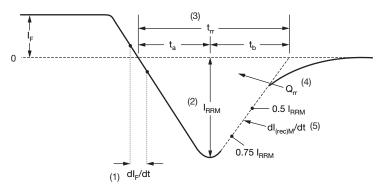


Fig. 7 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{\rm rr}$  reverse recovery time measured from zero crossing point of negative going  $I_{\rm F}$  to point where a line passing through 0.75  $I_{\rm RRM}$  and 0.50  $I_{\rm RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

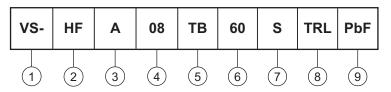
(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 3 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Process designator: A = Electron irradiated

Current rating (08 = 8 A)

Package outline (TB = TO-220, 2 leads)

Voltage rating (60 = 600 V)

7 -  $S = D^2PAK$ 

8 - • None = Tube

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

9 - • PbF = Lead (Pb)-free

• P = Lead (Pb)-free (for D<sup>2</sup>PAK TRR and TRL)

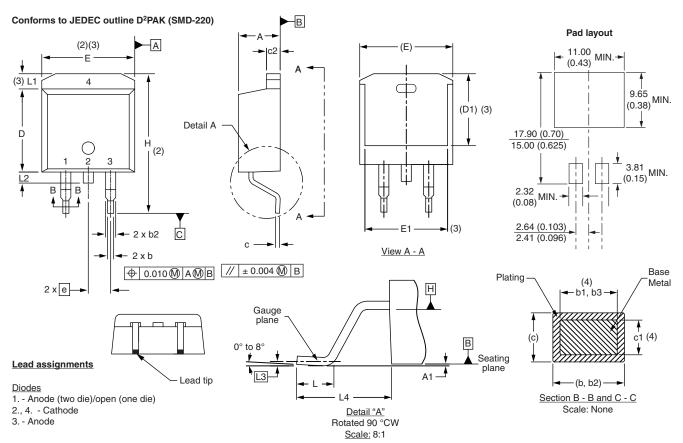
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95046</u>					
Part marking information	www.vishay.com/doc?95054				
Packaging information	www.vishay.com/doc?95032				

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08TB60SPBF	50	1000	Antistatic plastic tube				
VS-HFA08TB60STRRP	800	800	13" diameter reel				
VS-HFA08TB60STRLP	800	800	13" diameter reel				



## D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	MILLIMETERS		INCHES		
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	MILLIMETERS INCHES		INCHES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	1	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25	BSC	0.010 BSC		
L4	4.78	5.28	0.188	0.208	

#### Notes

- $^{(1)}$  Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB



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